

KP600-POWER THYRISTOR

Jiangsu Yangjie Runau Semiconductor Co.,Ltd

1200-1800 V_{DRM}

HIGH POWER THYRISTOR FOR PHASE CONTROL 1 0 0 1 3.8 60.0 Tm0 g0 2483.62 Tm0 g0 GβeV

Gating

Parameter

Jiangsu Yangjie Runau Semiconductor Co., Ltd
CASE OUTLINE AND DIMENSIONS

